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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74HC640/HD74HC643

Octal Bus Transceivers (with 3-state outputs)



ADE-205-517 (Z)
1st. Edition
Sep. 2000

Description

Each device has an active enable $\overline{G}$ and a direction control input, DIR. when DIR is high, data flows from the A inputs to the B outputs. When DIR is low, data flows from the B inputs to the A outputs. The HD74HC640 transfers inverted data from one bus to other and the HD74HC643 transfers inverted data from the A bus to the B bus and true data from the B bus to the A bus.

Features

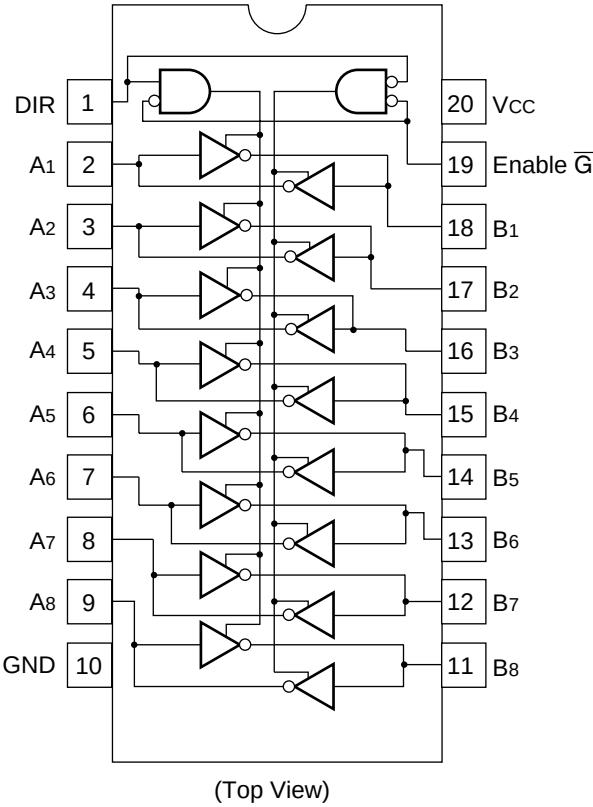
- High Speed Operation: $t_{pd} = 12 \text{ ns typ}$ ($C_L = 50 \text{ pF}$)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC}(\text{static}) = 4 \mu\text{A max}$ ($T_a = 25^\circ\text{C}$)

Function Table

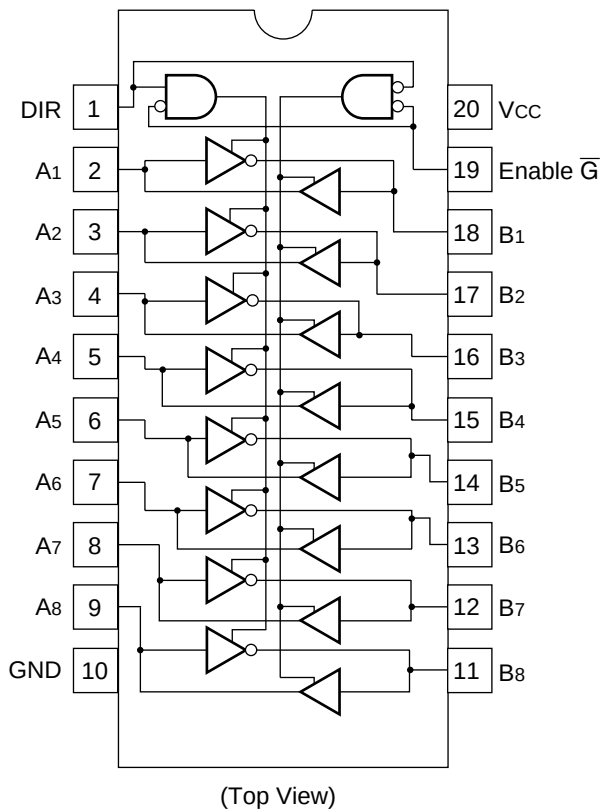
Control Inputs		Operation	
$\overline{G}$	DIR	HD74HC640	HD74HC643
L	L	$\overline{B}$ data to A bus	B data to A bus
L	H	$\overline{A}$ data to B bus	$\overline{A}$ data to B bus
H	X	Isolation	Isolation

Pin Arrangement

HD74HC640



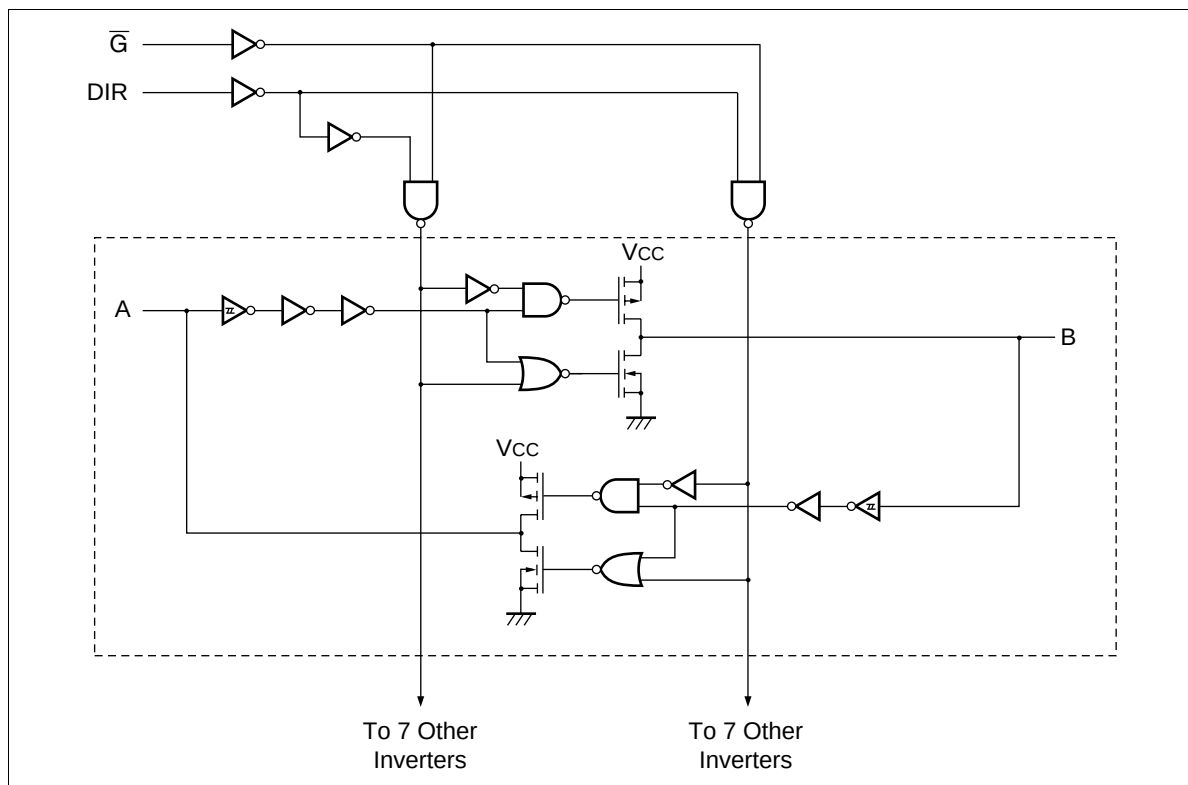
HD74HC643



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Output current	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC} , I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power Dissipation per package	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	$^{\circ}\text{C}$

HD74HC643



DC Characteristics

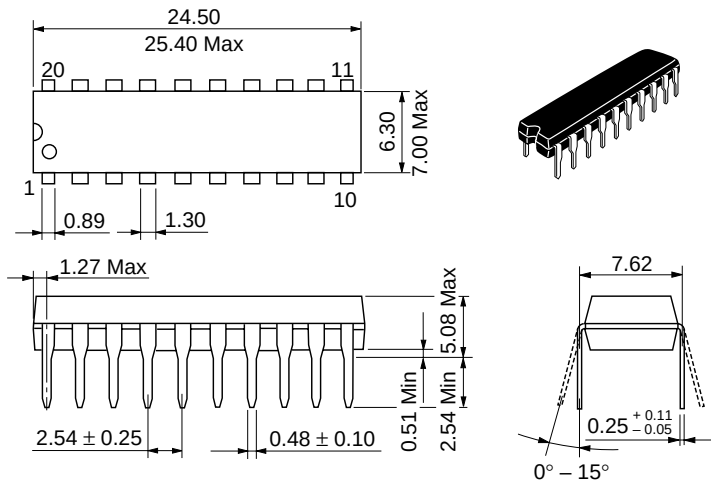
Item	Symbol	V _{CC} (V)	Ta = 25°C		Ta = -40 to +85°C		Unit	Test Conditions
			Min	Typ	Max	Min		
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V
		4.5	3.15	—	—	3.15	—	
		6.0	4.2	—	—	4.2	—	
	V _{IL}	2.0	—	—	0.3	—	0.3	V
		4.5	—	—	1.35	—	1.35	
		6.0	—	—	1.8	—	1.8	
Hysteresis voltage	V _H	2.0	—	0.1	—	—	—	V
		4.5	—	0.4	—	—	—	
		6.0	—	0.4	—	—	—	
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V
		4.5	4.4	4.5	—	4.4	—	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA
		6.0	5.9	6.0	—	5.9	—	
		4.5	4.18	—	—	4.13	—	I _{OH} = -6 mA
		6.0	5.68	—	—	5.63	—	I _{OH} = -7.8 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V
		4.5	—	0.0	0.1	—	0.1	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA
		6.0	—	0.0	0.1	—	0.1	
		4.5	—	—	0.26	—	0.33	I _{OL} = 6 mA
		6.0	—	—	0.26	—	0.33	I _{OL} = 7.8 mA
Off-state output current	I _{OZ}	6.0	—	—	±0.5	—	±5.0	μA
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	μA

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Item	Symbol	$V_{CC} \text{ (V)}$	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t_{PLH}	2.0	—	—	90	—	115	ns	
	t_{PHL}	4.5	—	12	18	—	23		
		6.0	—	—	15	—	20		
Output enable time	t_{ZH}	2.0	—	—	230	—	290	ns	
	t_{ZL}	4.5	—	15	46	—	58		
		6.0	—	—	39	—	49		
Output disable time	t_{HZ}	2.0	—	—	215	—	270	ns	
	t_{LZ}	4.5	—	17	43	—	54		
		6.0	—	—	37	—	46		
Output rise/fall time	t_{TLH}	2.0	—	—	60	—	75	ns	
	t_{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	C_{in}	—	—	5	10	—	10	pF	

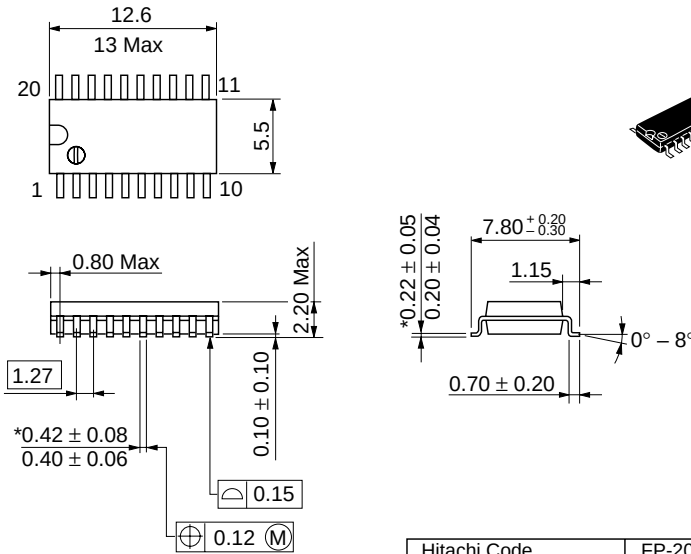
Package Dimensions

Unit: mm



Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.26 g

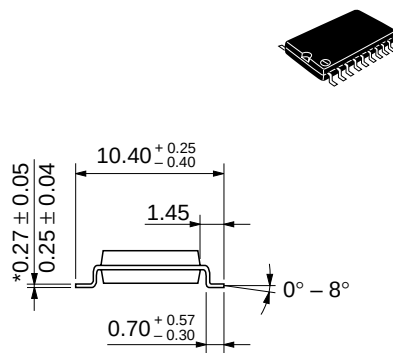
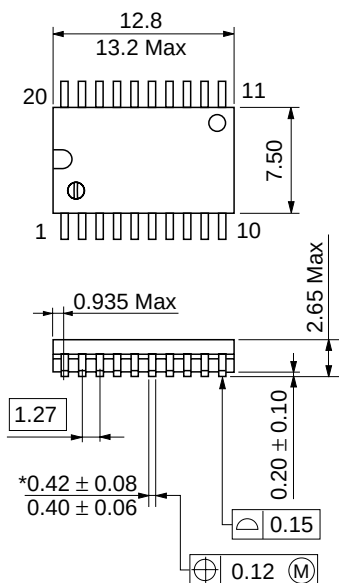
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.31 g

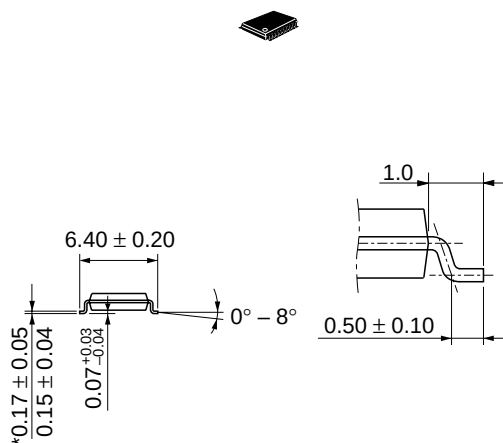
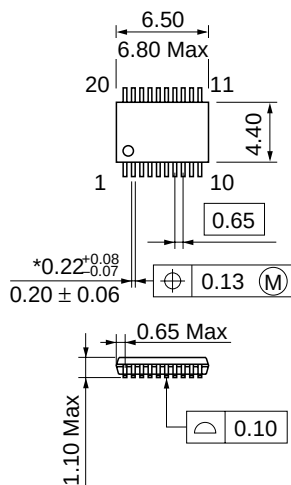
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.52 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Mass (reference value)	0.07 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
	Europe	:	http://www.hitachi-eu.com/hel/ecg
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For further information write to:Hitachi Semiconductor
(America) Inc.179 East Tasman Drive,
San Jose, CA 95134

Tel: <1> (408) 433-1990

Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components GroupDornacher Straße 3
D-85622 Feldkirchen, Munich

Germany

Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000

Fax: <44> (1628) 585160

Hitachi Asia Ltd.

Hitachi Tower

16 Collyer Quay #20-00,

Singapore 049318

Tel: <65>-538-6533/538-8577

Fax: <65>-538-6933/538-3877

URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.

(Taipei Branch Office)

4/F, No. 167, Tun Hwa North Road,

Hung-Kuo Building,

Taipei (105), Taiwan

Tel: <886>-(2)-2718-3666

Fax: <886>-(2)-2718-8180

Telex: 23222 HAS-TP

URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.

Group III (Electronic Components)

7/F., North Tower,

World Finance Centre,

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon,

Hong Kong

Tel: <852>-(2)-735-9218

Fax: <852>-(2)-730-0281

URL: <http://www.hitachi.com.hk>